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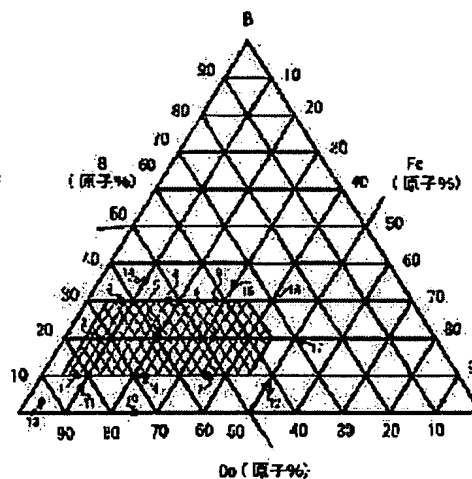
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(54) MAGNETORESISTIVE ELEMENT AND MAGNETIC MEMORY DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To simultaneously improve writing characteristics and reading characteristics by applying to a ferromagnetic layer a new material which has not been available heretofore.

SOLUTION: A magnetoresistive element comprises: a pair of the ferromagnetic layers opposed via an intermediate layer to obtain a magnetoresistance change by supplying current perpendicularly to a film surface. In this element, at least one of the magnetic layers contains a ferromagnetic material containing Fe, Co and B. The ferromagnetic material preferably contains $\text{Fe}_a\text{Co}_b\text{Ni}_c\text{B}_d$, wherein a, b, c and d each shows atomic %, $5 \leq a \leq 45$, $35 \leq b \leq 85$, $0 < c \leq 35$, and $10 \leq d \leq 30$ are satisfied, and $a+b+c+d=100$ is satisfied.



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